

<b>INFORMATION DISCLOSURE CITATION</b> <i>(Use several sheets if necessary)</i>				Docket Number (Optional) <b>D2337 D2</b>		Application Number <b>Unassigned</b>		
				Applicant(s) <b>Fwu-Iuan Hshieh et al.</b>				
				Filing Date <b>Filed Herewith</b>		Group Art Unit <b>2818</b>		
<b>U.S. PATENT DOCUMENTS</b>								
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE	
CK	1	6,144,065	11/7/2000	Kinzer	257	327		
CK	2	6,025,237	2/15/2000	Choi	438	301		
CK	3	5,072,266	12/10/1991	Bulucea et al.	357	23.4		
CK	4	4,971,929	11/20/90	D'Anna et al.	437	192		
CK	5	5,770,514	06/23/1998	Matsuda et al.	438	589		
CK	6	5,567,634	10-1996	Hebert et al.	437	41		
CK	7	<del>6,125,149</del> 6,215,149	04-2001	Lee et al.	257	328		
CK	8	6,225,649	05-2001	Minato	257	133		
CK	9	5,541,425	07/30/1996	Nishihara	257	139		
CK	10	5,468,982	11/21/1995	Hshieh et al.	257	331		
CK	11	5,866,931	02/02/1999	Bulucea et al.	257	331		
<b>FOREIGN PATENT DOCUMENTS</b>								
	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
CK	1	WO 94/03922	02/17/1994	PCT	H01L 21	265	✓	
CK	2	61190981	08/25/1986	JP	H01L 29	78		✓
CK	3	DE 19507146A1	11/1/1996	Germany	H01L 29	78		✓
<b>OTHER DOCUMENTS</b> <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i>								
CK	1	Matsumoto, S. et al., "A 70-V, 90-mμm <sup>2</sup> , High-Speed Double-Layer Gate UMOSFET Realized by Selective CVD Tungsten, Proceedings of the 6th International Symposium on Power Semiconductor Devices & IC's, Switzerland, May 31-June 2, 1994, pgs. 365-369.						
EXAMINER <i>Christy Karacek</i>				DATE CONSIDERED <i>3/21/04</i>				

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.